SILICON (Si) POWER MOSFET A CEB83A3



CEB83A3

30V ▲ 4.2mΩ ▲ 100A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO263 (D2PAK) package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability





RoHS

REACH

MAXIMUM RATINGS

Parameter (T_c = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	30V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current at T _c = 25°C	I _D	100A
Pulsed Drain Current Note 1	I _{DM}	400A
Maximum Power Dissipation at T _c = 25°C	PD	100W
Power Dissipation Derating above 25°C	ΔP _D	0.67W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +175°C

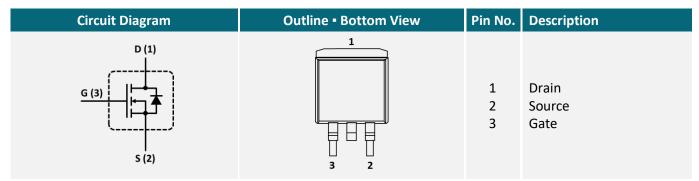
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.75°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	62.5°C/W

APPLICATIONS

Battery Management	DC/DC	High Side	Low Side	Power
Systems	Converter	Switches	Switches	Banks
+ 4 -				4

PIN DESCRIPTION



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ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250 \mu A$	BV _{DSS}	30			V
Zero Gate Voltage Drain Current	V_{DS} = 30V, V_{GS} = 0V	I _{DSS}			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			10	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-10	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	$V_{GS(th)}$	1		3	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 50A$	R _{DS(ON)}		4.2	5.3	mΩ
Static Drain-Source On-Resistance	V_{GS} = 4.5V, I_{D} = 40A	R _{DS(ON)}		6	8	mΩ
Dynamic Characteristics Note 3						
Input Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	C _{ISS}		6350		pF
Output Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	Coss		980		рF
Reverse Transfer Capacitance	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	C _{RSS}		600		pF
Forward Transconductance	$V_{DS} = 10V, I_{D} = 15A$	g _{FS}		27		S
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G}(\text{ext})}$ = 6 Ω	t _{D(ON)}		22		ns
Turn-On Rise Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 6 Ω	t _R		24		ns
Turn-Off Delay Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 6 Ω	t _{D(OFF)}		209		ns
Turn-Off Fall Time	V_{DD} = 15V, V_{GS} = 10V, I_{D} = 1A, $R_{\text{G(ext)}}$ = 6 Ω	t _F		173		ns
Total Gate Charge	V_{DS} = 15V, V_{GS} = 5V, I_{D} = 16A	Q _G		53		nC
Gate Source Charge	V_{DS} = 15V, V_{GS} = 5V, I_{D} = 16A	Q _{GS}		15		nC
Gate Drain Charge	V_{DS} = 15V, V_{GS} = 5V, I_{D} = 16A	\mathbf{Q}_{GD}		22		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		ls			100	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 20A	V_{SD}			1.5	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

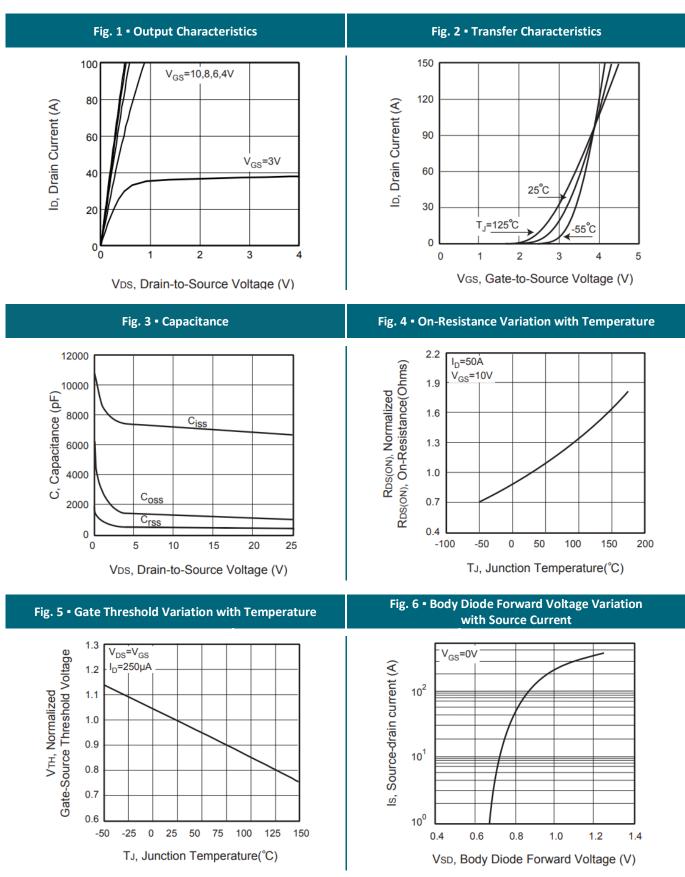
3: Guaranteed by design, not subject to production testing.



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REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



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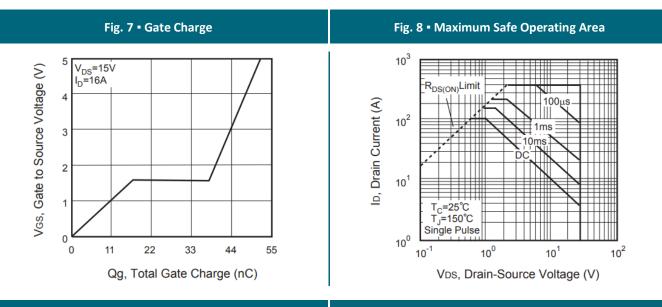
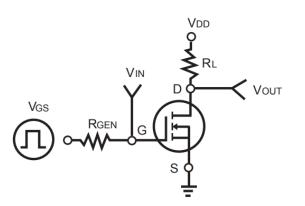


Fig. 9 - Switching Test Circuit



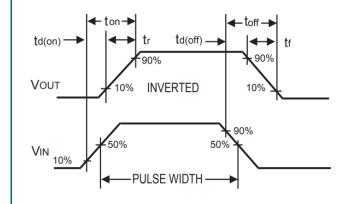
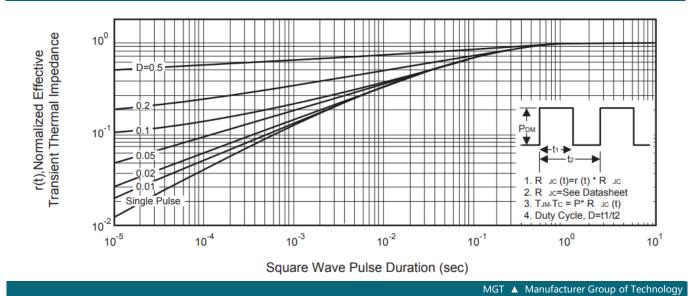


Fig. 10 - Switching Waveforms

Fig. 11 • Normalized Thermal Transient Impedance Curve



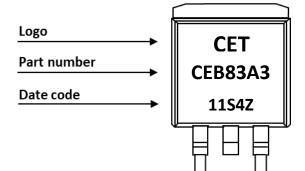




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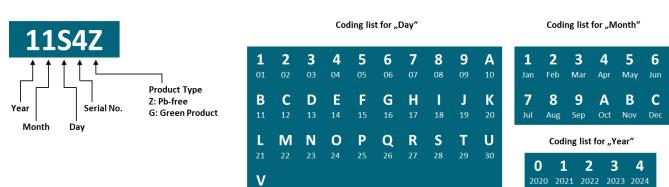
5 6 7 8

PART MARKING



DATE CODE

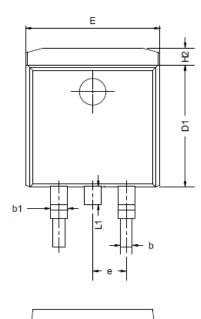
Example: 11S4Z

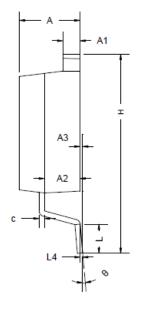


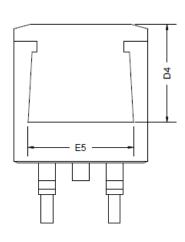
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PACKAGE OUTLINE







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	E	9.86	10.16	10.36
A1	1.22	1.27	1.42	E5	7.06	-	-
A2	2.49	2.69	2.89	е		2.54 BSC	
A3	0.00	0.13	0.25	н	14.70	15.10	15.50
b	0.70	0.81	0.96	H2	1.07	1.27	1.47
b1	1.17	1.27	1.47	L	2.00	2.30	2.60
С	0.30	0.38	0.53	L1	1.40	1.55	1.70
D1	8.50	8.70	8.90	L4		0.25 BSC	
D4	6.60	-	-	θ	0°	5°	9°

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEB83A3	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs

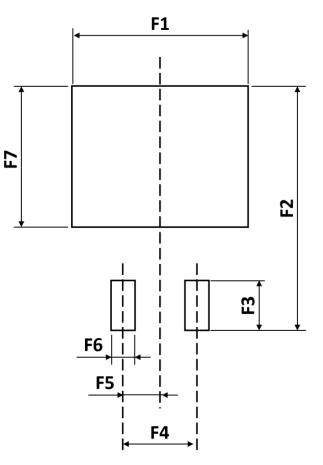
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RECOMMENDED PAD LAYOUT



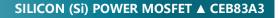
Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-	F5	-	2.54	-
F2	-	16.90	-	F6	-	1.60	-
F3	-	2.54	-	F7	-	9.75	-
F4	-	5.08	-				

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

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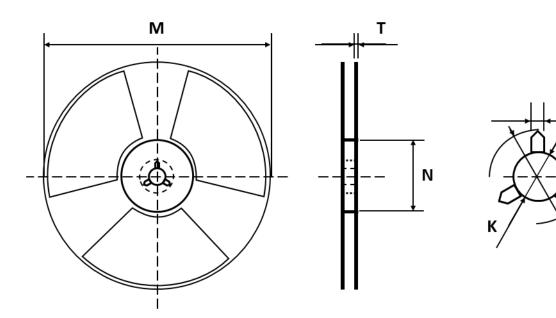


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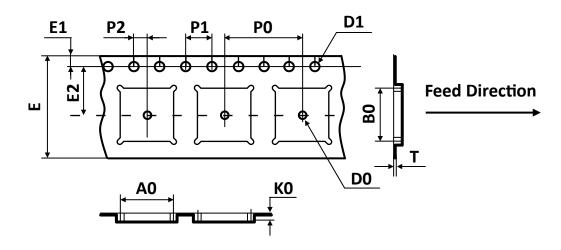


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	Ø330 ±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

TAPE DIMENSIONS All dimensions in mm



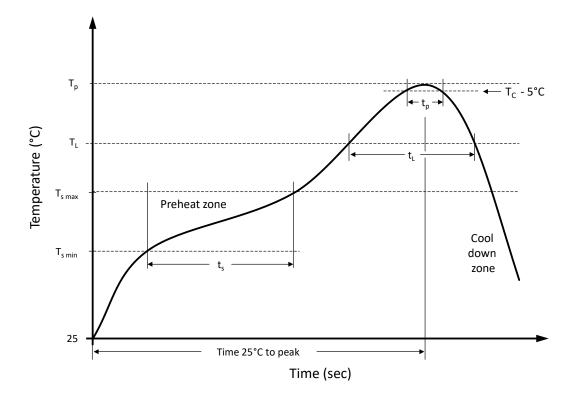
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D ² PAK	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05







RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time t_L maintained above T_L	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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